

IN THE CLAIMS:

Claims 1 through 20 are currently pending in this application, wherein Claims 9, 10, 13, 14 and 19 have been previously withdrawn from further consideration pending the allowability of a generic claim. Please cancel Claim 8 without prejudice or disclaimer, and please amend Claims 1, 11, 15 and 18, as follows:

1. (Currently Amended) A fabrication process for a semiconductor integrated circuit device, comprising:
 - (a) providing a semiconductor substrate;
 - (b) forming a gate insulator film on a main surface of the semiconductor substrate;
 - (c) forming a conducting film at least containing a metal film or a metal compound film on the gate insulator film;
 - (d) patterning the conducting film thereby forming a gate electrode;
 - (e) nitriding or carbonizing a side wall for the gate electrode at a temperature of 600°C or lower; and
 - (f) restoring damage in the gate insulator film near the end of the gate electrode caused by patterning by oxidizing the main surface of the semiconductor substrate to restore the gate insulator film.
2. (Original) A fabrication process according to claim 1, wherein the side wall for the gate electrode is nitrided or carbonized at a temperature in the range of about 200°C to 500°C.
3. (Original) A fabrication process according to claim 1, wherein a plasma treatment using a nitrogen-containing gas is used for nitriding, thereby nitriding the side wall for the gate electrode.
4. (Original) A fabrication process according to claim 1, wherein a plasma treatment or a heat treatment using a carbon-containing gas is used for carbonizing, thereby carbonizing the side wall for the gate electrode.

5. (Original) A fabrication process according to claim 1, wherein the main surface of the semiconductor substrate is oxidized by plasma processing using an oxygen-containing gas when oxidizing the main surface of the semiconductor substrate.
6. (Original) A fabrication process according to claim 1, wherein the main surface of the semiconductor substrate is oxidized at a temperature of 600°C or lower.
7. (Original) A fabrication process according to claim 1, wherein the main surface of the semiconductor substrate is oxidized at a temperature in the range of about 200°C to 500°C.
8. (Cancelled)
9. (Withdrawn) A fabrication process for a semiconductor integrated circuit device comprising:
 - (a) providing a semiconductor substrate;
 - (b) forming a gate insulator film on a main surface of the semiconductor substrate;
 - (c) forming a conducting film at least containing a metal film or a metal compound film on the gate insulator film;
 - (d) patterning the conducting film thereby forming a gate electrode;
 - (e) nitriding or carbonizing a side wall for the gate electrode at a temperature of 600°C or lower;
 - (f) oxidizing the main surface of the semiconductor substrate; andfurther comprising including a step (d1) of adhering silicon or silicon compound on the side wall for the gate electrode by a plasma processing using a silicon-containing gas after patterning the conducting film thereby forming a gate electrode before nitriding or carbonizing the side wall.
10. (Withdrawn) The fabrication process according to claim 9, wherein silicon or silicon compound is adhered on the side wall for the gate electrode by a plasma processing using a silicon halide gas or a silicon hydride gas in the step (d1).

11. (Currently Amended) A fabrication process according to claim 1, wherein the gate electrode is made by:
providing a stacking structure comprising providing a polycrystalline silicon film, providing a metal nitride film on the polycrystalline silicon film, and providing a metal film on the metal nitride film.
12. (Original) A fabrication process according to claim 11, wherein the metal nitride film comprises a nitride from the group consisting of tungsten, molybdenum, tantalum or titanium, and the metal film comprises a metal film from the group consisting of tungsten, molybdenum, tantalum or titanium.
13. (Withdrawn) A fabrication process according to claim 11, wherein the gate electrode further comprises a metal silicide film between the polycrystalline silicon film and the metal nitride film.
14. (Withdrawn) A fabrication process according to claim 13, wherein the metal silicide film comprises a silicide from the group consisting of tungsten, molybdenum, tantalum, titanium, zirconium or hafnium.
15. (Currently Amended) A fabrication process according to claim 1, further comprising:
providing the gate electrode with a stacked structure comprising: providing a polycrystalline silicon film; providing a metal carbide film on the polycrystalline silicon film; and providing a metal film on the metal carbide ~~nitride~~ film.
16. (Original) A fabrication process according to claim 1, further comprising:
providing the gate electrode with a single layered structure of a metal film.
17. (Original) A fabrication process according to claim 1, further comprising:
providing the gate electrode with a stacked structure comprising a polycrystalline silicon film and a metal silicide film on the polycrystalline silicon film.
18. (Currently Amended) A fabrication process for a semiconductor integrated circuit device, comprising:

- (a) providing a semiconductor substrate;
- (b) forming a gate insulator film on a main surface of the semiconductor substrate;
- (c) forming a conducting film at least containing a metal film or a metal compound film on the gate insulator film;
- (d) patterning the conducting film thereby forming a gate electrode;
- (e) nitriding or carbonizing a side wall for the gate electrode at a temperature of 600°C or lower; and
- (f) restoring damage in the gate insulator film near the end of the gate electrode caused by patterning by oxidizing the main surface of the semiconductor substrate to restore the gate insulator film;

and further comprising forming a first insulator film on the conducting film after forming the conducting film and before patterning the conducting film thereby forming a gate electrode, so that the first insulator film remains on the gate electrode and only the side wall of the gate electrode is exposed when nitriding or carbonizing the side wall for the gate electrode at a temperature of 600°C or lower.

19. (Withdrawn) A fabrication process according to claim 1, further comprising:
 - providing a plasma treatment by applying a nitrogen oxide gas or a carbon oxide gas before nitriding or carbonizing the side wall for the gate electrode at a temperature of 600°C or lower; and
 - providing a nitrogen oxide gas or a carbon oxide gas having a reducing property.
20. (Original) A fabrication process according to claim 1, further comprising:
 - providing at least a portion of the gate insulator film situated below a portion of the conducting film to be removed when patterning the conducting film thereby forming a gate electrode.